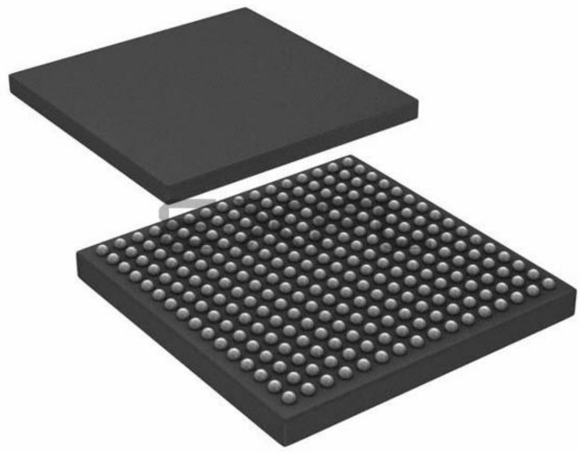

Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	13824
Total RAM Bits	110592
Number of I/O	177
Number of Gates	600000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl600v5-fg256

I/Os Per Package[1]

IGLOO Devices	AGL015[2]	AGL030	AGL060	AGL125	AGL250		AGL400		AGL600		AGL1000	
ARM-Enabled IGLOO Devices					M1AGL250				M1AGL600		M1AGL1000	
	I/O Type[3]											
Package	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O [4]	Differential I/O Pairs	Single-Ended I/O [4]	Differential I/O Pairs	Single-Ended I/O [4]	Differential I/O Pairs	Single-Ended I/O [4]	Differential I/O Pairs
QN48	–	34	–	–	–	–	–	–	–	–	–	–
QN68	49	49	–	–	–	–	–	–	–	–	–	–
UC81	–	66	–	–	–	–	–	–	–	–	–	–
CS81	–	66	–	–	–	–	–	–	–	–	–	–
CS121	–	–	96	96	–	–	–	–	–	–	–	–
VQ100	–	77	71	71	68	13	–	–	–	–	–	–
QN132[6]	–	81	80	84	–	–	–	–	–	–	–	–
CS196	–	–	–	133	143 [5]	35 [5]	143	35	–	–	–	–
FG144	–	–	–	97	97	24	97	25	97	25	97	25
FG256[7]	–	–	–	–	–	–	178	38	177	43	177	44
CS281	–	–	–	–	–	–	–	–	215	53	215	53
FG484[7]	–	–	–	–	–	–	194	38	235	60	300	74

Notes:

1. *When considering migrating your design to a lower- or higher-density device, refer to the* IGLOO FPGA Fabric User Guide *to ensure compliance with design and board migration requirements.*
2. *AGL015 is not recommended for new designs.*
3. *When the Flash*Freeze pin is used to directly enable Flash*Freeze mode and not used as a regular I/O, the number of single-ended user I/Os available is reduced by one.*
4. *Each used differential I/O pair reduces the number of single-ended I/Os available by two.*
5. *The M1AGL250 device does not support QN132 or CS196 packages.*
6. *Package not available.*
7. *FG256 and FG484 are footprint-compatible packages.*

Table 1 • IGLOO FPGAs Package Sizes Dimensions

Package	UC81	CS81	CS121	QN48	QN68	QN132*	CS196	CS281	FG144	VQ100	FG256	FG484
Length × Width (mm\mm)	4 × 4	5 × 5	6 × 6	6 × 6	8 × 8	8 × 8	8 × 8	10 × 10	13 × 13	14 × 14	17 × 17	23 × 23
Nominal Area (mm^2)	16	25	36	36	64	64	64	100	169	196	289	529
Pitch (mm)	0.4	0.5	0.5	0.4	0.4	0.5	0.5	0.5	1.0	0.5	1.0	1.0
Height (mm)	0.80	0.80	0.99	0.90	0.90	0.75	1.20	1.05	1.45	1.00	1.60	2.23

*Note: * Package not available.*

Ramping up (V2 devices): 0.65 V < trip_point_up < 1.05 V
Ramping down (V2 devices): 0.55 V < trip_point_down < 0.95 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLX exceed brownout activation levels (see Figure 2-1 and Figure 2-2 on page 2-5 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels (0.75 V ± 0.25 V for V5 devices, and 0.75 V ± 0.2 V for V2 devices), the PLL output lock signal goes low and/or the output clock is lost. Refer to the Brownout Voltage section in the "Power-Up/-Down Behavior of Low Power Flash Devices" chapter of the *ProASIC®3* and *ProASIC3E* FPGA fabric user guides for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers
3. Output buffers, after 200 ns delay from input buffer activation

To make sure the transition from input buffers to output buffers is clean, ensure that there is no path longer than 100 ns from input buffer to output buffer in your design.

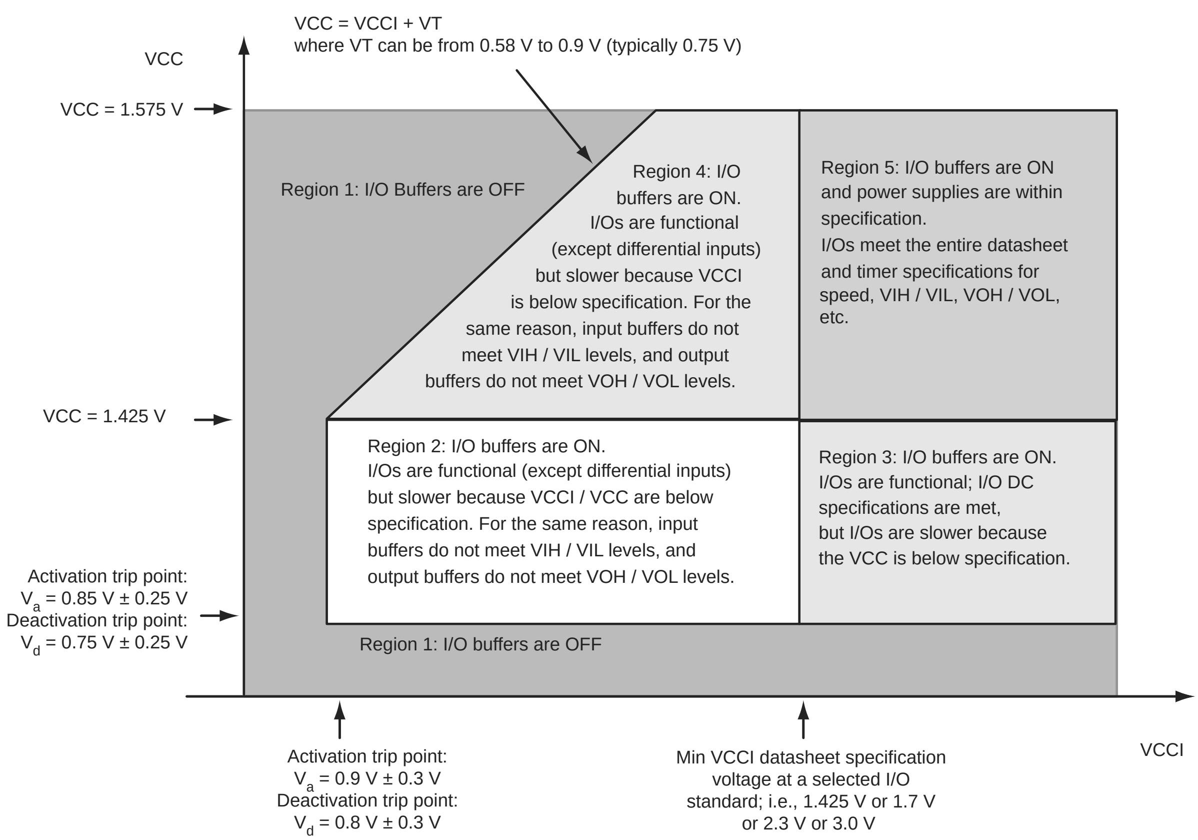

Figure 2-1 • V5 Devices – I/O State as a Function of VCCI and VCC Voltage Levels

Table 2-17 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings[1] Applicable to Standard Plus I/O Banks

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC7 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	5	3.3	–	122.16
3.3 V LVCMOS Wide Range[4]	5	3.3	–	122.16
2.5 V LVCMOS	5	2.5	–	68.37
1.8 V LVCMOS	5	1.8	–	34.53
1.5 V LVCMOS (JESD8-11)	5	1.5	–	23.66
1.2 V LVCMOS[5]	5	1.2	–	14.90
1.2 V LVCMOS Wide Range[5]	5	1.2	–	14.90
3.3 V PCI	10	3.3	–	181.06
3.3 V PCI-X	10	3.3	–	181.06

Notes:

1. *Dynamic power consumption is given for standard load and software default drive strength and output slew.*
2. *P_{DC7} is the static power (where applicable) measured on VCCI.*
3. *P_{AC10} is the total dynamic power measured on VCCI.*
4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
5. *Applicable for IGLOO V2 devices only.*

Table 2-18 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings[1] Applicable to Standard I/O Banks

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC7 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	5	3.3	–	104.38
3.3 V LVCMOS Wide Range[4]	5	3.3	–	104.38
2.5 V LVCMOS	5	2.5	–	59.86
1.8 V LVCMOS	5	1.8	–	31.26
1.5 V LVCMOS (JESD8-11)	5	1.5	–	21.96
1.2 V LVCMOS[5]	5	1.2	–	13.49
1.2 V LVCMOS Wide Range[5]	5	1.2	–	13.49

Notes:

1. *Dynamic power consumption is given for standard load and software default drive strength and output slew.*
2. *PDC7 is the static power (where applicable) measured on VCCI.*
3. *PAC10 is the total dynamic power measured on VCCI.*
4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
5. *Applicable for IGLOO V2 devices only.*

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Microsemi Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-23 on page 2-19.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-24 on page 2-19.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-24 on page 2-19. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

$P_{STAT} = (P_{DC1}$ or P_{DC2} or $P_{DC3}) + N_{BANKS} * P_{DC5} + N_{INPUTS} * P_{DC6} + N_{OUTPUTS} * P_{DC7}$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

N_{BANKS} is the number of I/O banks powered in the design.

Total Dynamic Power Consumption—P_{DYN}

$P_{DYN} = P_{CLOCK} + P_{S\text{-}CELL} + P_{C\text{-}CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$

Global Clock Contribution—P_{CLOCK}

$P_{CLOCK} = (P_{AC1} + N_{SPINE} * P_{AC2} + N_{ROW} * P_{AC3} + N_{S\text{-}CELL} * P_{AC4}) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the *IGLOO FPGA Fabric User Guide.*

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the *IGLOO FPGA Fabric User Guide.*

F_{CLK} is the global clock signal frequency.

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

P_{AC1}, P_{AC2}, P_{AC3}, and P_{AC4} are device-dependent.

Sequential Cells Contribution—$P_{S\text{-}CELL}$

$P_{S\text{-}CELL} = N_{S\text{-}CELL} * (P_{AC5} + \alpha_1 / 2 * P_{AC6}) * F_{CLK}$

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-23 on page 2-19.

F_{CLK} is the global clock signal frequency.

Table 2-27 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings Applicable to Standard I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[2]	Slew Rate	VIL Min. V	VIL Max. V	V_{IH} Min. V	V_{IH} Max. V	VOL Max. V	V_{OH} Min. V	I_{OL}[1] mA	I_{OH}[1] mA
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8 mA	High	–0.3	0.8	2	3.6	0.4	2.4	8	8
3.3 V LVCMOS Wide Range[3]	100 µA	8 mA	High	–0.3	0.8	2	3.6	0.2	VDD-0.2	0.1	0.1
2.5 V LVCMOS	8 mA	8 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4
1.5 V LVCMOS	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS[4]	1 mA	1 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1
1.2 V LVCMOS Wide Range[4,5]	100 µA	1 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI – 0.1	0.1	0.1

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
3. *All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
4. *Applicable to V2 Devices operating at VCCI ≥ VCC.*
5. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.*

Table 2-34 • **Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI (per standard) Applicable to Advanced I/O Banks**

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[1]	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	5	–	1.55	2.67	0.26	0.98	1.10	2.71	2.18	3.25	3.93	8.50	7.97	ns
3.3 V LVCMOS Wide Range[2]	100 µA	12 mA	High	5	–	1.55	3.73	0.26	1.32	1.10	3.73	2.91	4.51	5.43	9.52	8.69	ns
2.5 V LVCMOS	12 mA	12 mA	High	5	–	1.55	2.64	0.26	1.20	1.10	2.67	2.29	3.30	3.79	8.46	8.08	ns
1.8 V LVCMOS	12 mA	12 mA	High	5	–	1.55	2.72	0.26	1.11	1.10	2.76	2.43	3.58	4.19	8.55	8.22	ns
1.5 V LVCMOS	12 mA	12 mA	High	5	–	1.55	2.96	0.26	1.27	1.10	3.00	2.70	3.75	4.23	8.78	8.48	ns
1.2 V LVCMOS	2 mA	2 mA	High	5	–	1.55	3.60	0.26	1.60	1.10	3.47	3.36	3.93	3.65	9.26	9.14	ns
1.2 V LVCMOS Wide Range[3]	100 µA	2 mA	High	5	–	1.55	3.60	0.26	1.60	1.10	3.47	3.36	3.93	3.65	9.26	9.14	ns
3.3 V PCI	Per PCI spec	–	High	10	25[2]	1.55	2.91	0.26	0.86	1.10	2.95	2.29	3.25	3.93	8.74	8.08	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25[2]	1.55	2.91	0.25	0.86	1.10	2.95	2.29	3.25	3.93	8.74	8.08	ns
LVDS	24 mA	–	High	–	–	1.55	2.27	0.25	1.57	–	–	–	–	–	–	–	ns
LVPECL	24 mA	–	High	–	–	1.55	2.24	0.25	1.38	–	–	–	–	–	–	–	ns

Notes:

1. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
3. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification*
4. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-12 on page 2-79 for connectivity. This resistor is not required during normal operation.*
5. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-42 • **I/O Short Currents IOSH/IOSL Applicable to Advanced I/O Banks**

	Drive Strength	IOSL (mA)*	IOSH (mA)*
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
	12 mA	103	109
	16 mA	132	127
	24 mA	268	181
3.3 V LVCMOS Wide Range	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
	12 mA	65	74
	16 mA	83	87
	24 mA	169	124
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
	6 mA	35	44
	8 mA	45	51
	12 mA	91	74
	16 mA	91	74
1.5 V LVCMOS	2 mA	13	16
	4 mA	25	33
	6 mA	32	39
	8 mA	66	55
	12 mA	66	55
1.2 V LVCMOS	2 mA	20	26
1.2 V LVCMOS Wide Range	100 µA	20	26
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	103	109

Note: *T_J = 100°C*

2.5 V LVCMOS

Low-Voltage CMOS for 2.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 2.5 V applications.

Table 2-79 • **Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks**

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	μA[4]	μA[4]
2 mA	–0.3	0.7	1.7	2.7	0.7	1.7	2	2	16	18	10	10
4 mA	–0.3	0.7	1.7	2.7	0.7	1.7	4	4	16	18	10	10
6 mA	–0.3	0.7	1.7	2.7	0.7	1.7	6	6	32	37	10	10
8 mA	–0.3	0.7	1.7	2.7	0.7	1.7	8	8	32	37	10	10
12 mA	–0.3	0.7	1.7	2.7	0.7	1.7	12	12	65	74	10	10
16 mA	–0.3	0.7	1.7	2.7	0.7	1.7	16	16	83	87	10	10
24 mA	–0.3	0.7	1.7	2.7	0.7	1.7	24	24	169	124	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-80 • **Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O Banks**

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	μA[4]	μA[4]
2 mA	–0.3	0.7	1.7	2.7	0.7	1.7	2	2	16	18	10	10
4 mA	–0.3	0.7	1.7	2.7	0.7	1.7	4	4	16	18	10	10
6 mA	–0.3	0.7	1.7	2.7	0.7	1.7	6	6	32	37	10	10
8 mA	–0.3	0.7	1.7	2.7	0.7	1.7	8	8	32	37	10	10
12 mA	–0.3	0.7	1.7	2.7	0.7	1.7	12	12	65	74	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-92 • 2.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	2.91	0.26	1.19	1.10	2.95	2.66	2.50	2.72	8.74	8.45	ns
4 mA	Std.	1.55	2.91	0.26	1.19	1.10	2.95	2.66	2.50	2.72	8.74	8.45	ns
6 mA	Std.	1.55	2.51	0.26	1.19	1.10	2.54	2.18	2.75	3.21	8.33	7.97	ns
8 mA	Std.	1.55	2.51	0.26	1.19	1.10	2.54	2.18	2.75	3.21	8.33	7.97	ns
12 mA	Std.	1.55	2.29	0.26	1.19	1.10	2.32	1.94	2.94	3.52	8.10	7.73	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.*

Table 2-93 • 2.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	4.85	0.26	1.15	1.10	4.93	4.55	2.13	2.24	ns
4 mA	Std.	1.55	4.85	0.26	1.15	1.10	4.93	4.55	2.13	2.24	ns
6 mA	Std.	1.55	4.09	0.26	1.15	1.10	4.16	3.95	2.38	2.71	ns
8 mA	Std.	1.55	4.09	0.26	1.15	1.10	4.16	3.95	2.38	2.71	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-94 • 2.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	2.76	0.26	1.15	1.10	2.80	2.52	2.13	2.32	ns
4 mA	Std.	1.55	2.76	0.26	1.15	1.10	2.80	2.52	2.13	2.32	ns
6 mA	Std.	1.55	2.39	0.26	1.15	1.10	2.42	2.05	2.38	2.80	ns
8 mA	Std.	1.55	2.39	0.26	1.15	1.10	2.42	2.05	2.38	2.80	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.*

Table 2-100 **• 1.8 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	3.25	0.18	1.01	0.66	3.21	3.25	2.33	1.61	6.80	6.85	ns
4 mA	Std.	0.97	2.62	0.18	1.01	0.66	2.68	2.51	2.66	2.46	6.27	6.11	ns
6 mA	Std.	0.97	2.31	0.18	1.01	0.66	2.36	2.15	2.90	2.87	5.95	5.75	ns
8 mA	Std.	0.97	2.25	0.18	1.01	0.66	2.30	2.08	2.95	2.98	5.89	5.68	ns
12 mA	Std.	0.97	2.24	0.18	1.01	0.66	2.29	2.00	3.02	3.40	5.88	5.60	ns
16 mA	Std.	0.97	2.24	0.18	1.01	0.66	2.29	2.00	3.02	3.40	5.88	5.60	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-101 **• 1.8 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	5.78	0.18	1.01	0.66	5.90	5.32	1.95	1.47	9.49	8.91	ns
4 mA	Std.	0.97	4.75	0.18	1.01	0.66	4.85	4.54	2.25	2.21	8.44	8.13	ns
6 mA	Std.	0.97	4.07	0.18	1.01	0.66	4.15	3.98	2.46	2.58	7.75	7.57	ns
8 mA	Std.	0.97	4.07	0.18	1.01	0.66	4.15	3.98	2.46	2.58	7.75	7.57	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-102 **• 1.8 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.76	0.18	1.01	0.66	2.79	2.76	1.94	1.51	6.39	6.35	ns
4 mA	Std.	0.97	2.25	0.18	1.01	0.66	2.30	2.09	2.24	2.29	5.89	5.69	ns
6 mA	Std.	0.97	1.97	0.18	1.01	0.66	2.02	1.76	2.46	2.66	5.61	5.36	ns
8 mA	Std.	0.97	1.97	0.18	1.01	0.66	2.02	1.76	2.46	2.66	5.61	5.36	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-103 **• 1.8 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	5.63	0.18	0.98	0.66	5.74	5.30	1.68	1.24	ns
4 mA	Std.	0.97	4.69	0.18	0.98	0.66	4.79	4.52	1.97	1.98	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

Table 2-111 • **Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks**

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	μA[4]	μA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	4	4	25	33	10	10
6 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	6	6	32	39	10	10
8 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	8	8	66	55	10	10
12 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	12	12	66	55	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-112 • **Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O Banks**

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	μA[4]	μA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	4	4	25	33	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Embedded SRAM and FIFO Characteristics

SRAM

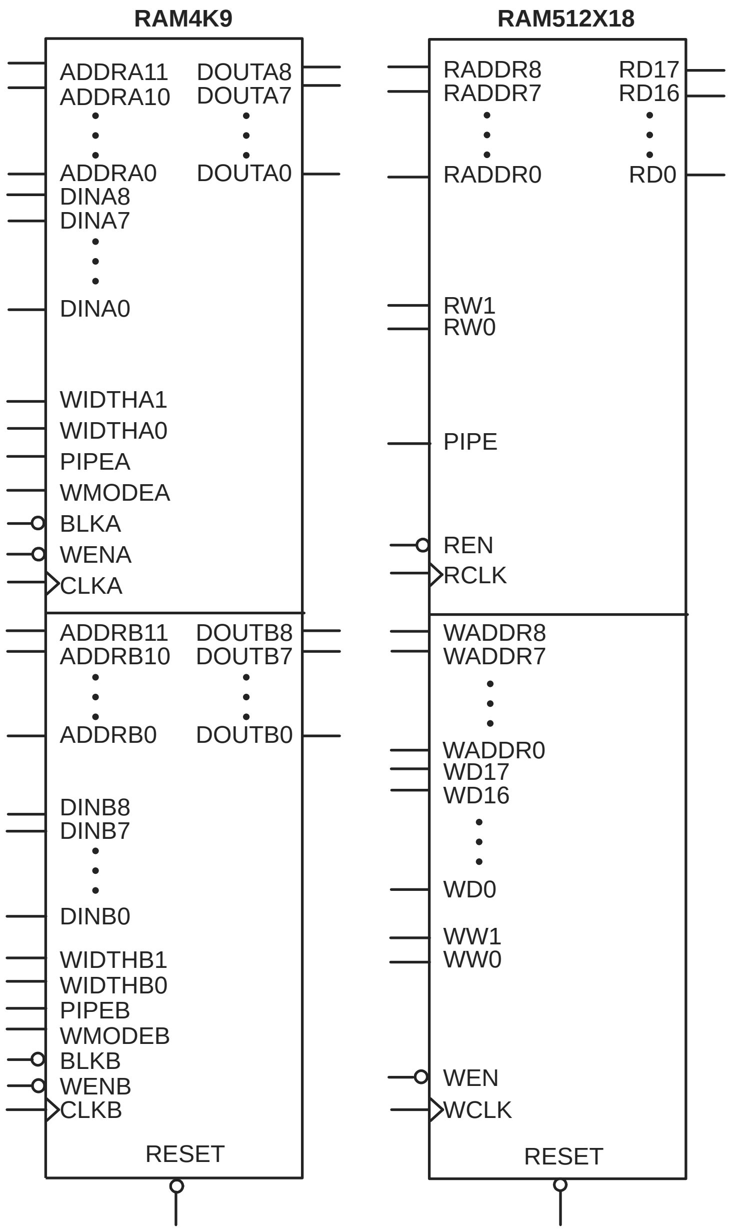

Figure 2-31 • **RAM Models**

Table 2-194 • RAM512X18
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	1.53	ns
t_{AH}	Address hold time	0.29	ns
t_{ENS}	REN, WEN setup time	1.36	ns
t_{ENH}	REN, WEN hold time	0.15	ns
t_{DS}	Input data (WD) setup time	1.33	ns
t_{DH}	Input data (WD) hold time	0.66	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	7.88	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	3.20	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address – Applicable to Opening Edge	0.87	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address – Applicable to Opening Edge	1.04	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow through)	3.86	ns
	RESET Low to data out Low on RD (pipelined)	3.86	ns
$t_{REMRSTB}$	RESET removal	1.12	ns
$t_{RECRSTB}$	RESET recovery	5.93	ns
$t_{MPWRSTB}$	RESET minimum pulse width	1.18	ns
t_{CYC}	Clock cycle time	10.90	ns
F_{MAX}	Maximum frequency	92	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs*.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

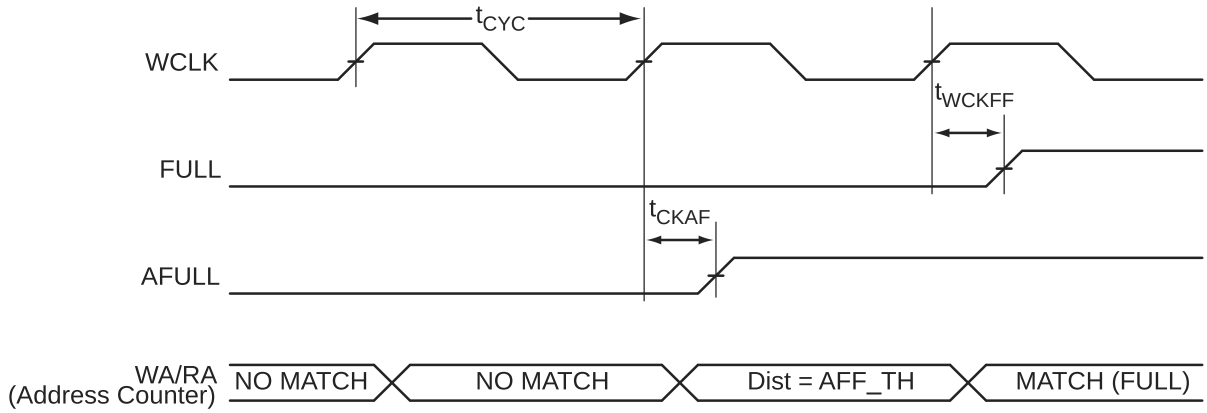

Figure 2-42 **• FIFO FULL Flag and AFULL Flag Assertion**

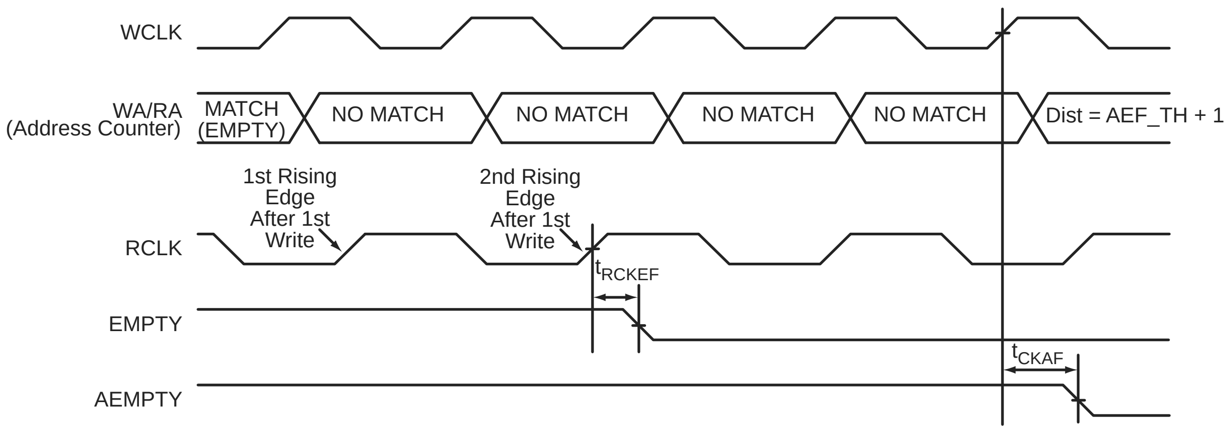

Figure 2-43 **• FIFO EMPTY Flag and AEMPTY Flag Deassertion**

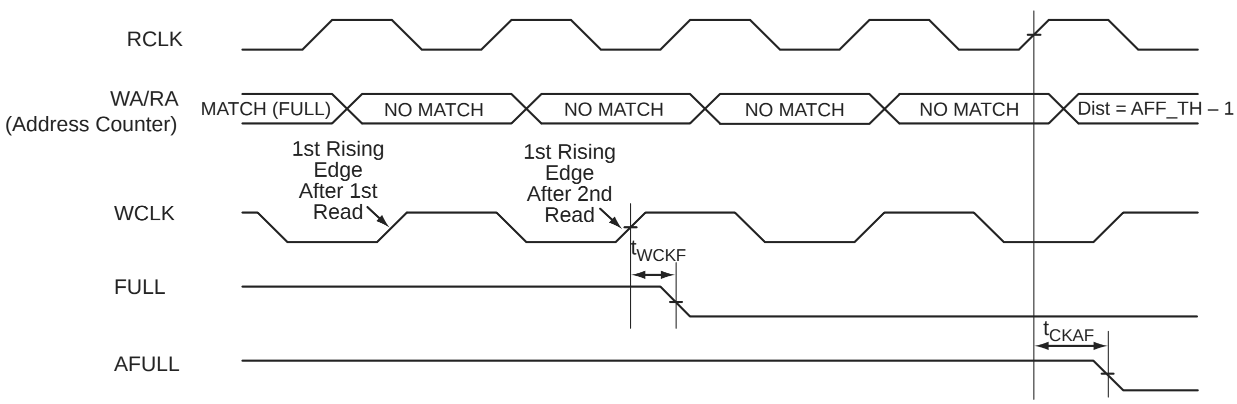

Figure 2-44 **• FIFO FULL Flag and AFULL Flag Deassertion**

QN48	
Pin Number	AGL030 Function
1	IO82RSB1
2	GEC0/IO73RSB1
3	GEA0/IO72RSB1
4	GEB0/IO71RSB1
5	GND
6	VCCIB1
7	IO68RSB1
8	IO67RSB1
9	IO66RSB1
10	IO65RSB1
11	IO64RSB1
12	IO62RSB1
13	IO61RSB1
14	FF/IO60RSB1
15	IO57RSB1
16	IO55RSB1
17	IO53RSB1
18	VCC
19	VCCIB1
20	IO46RSB1
21	IO42RSB1
22	TCK
23	TDI
24	TMS
25	VPUMP
26	TDO
27	TRST
28	VJTAG
29	IO38RSB0
30	GDB0/IO34RSB0
31	GDA0/IO33RSB0
32	GDC0/IO32RSB0
33	VCCIB0
34	GND
35	VCC
36	IO25RSB0

QN48	
Pin Number	AGL030 Function
37	IO24RSB0
38	IO22RSB0
39	IO20RSB0
40	IO18RSB0
41	IO16RSB0
42	IO14RSB0
43	IO10RSB0
44	IO08RSB0
45	IO06RSB0
46	IO04RSB0
47	IO02RSB0
48	IO00RSB0

FG484	
Pin Number	**AGL400 Function**
R9	VCCIB2
R10	VCCIB2
R11	IO108RSB2
R12	IO101RSB2
R13	VCCIB2
R14	VCCIB2
R15	VMV2
R16	IO83RSB2
R17	GDB1/IO78UPB1
R18	GDC1/IO77UDB1
R19	IO75NDB1
R20	VCC
R21	NC
R22	NC
T1	NC
T2	NC
T3	NC
T4	IO140NDB3
T5	IO138PPB3
T6	GEC1/IO137PPB3
T7	IO131RSB2
T8	GNDQ
T9	GEA2/IO134RSB2
T10	IO117RSB2
T11	IO111RSB2
T12	IO99RSB2
T13	IO94RSB2
T14	IO87RSB2
T15	GNDQ
T16	IO93RSB2
T17	VJTAG
T18	GDC0/IO77VDB1
T19	GDA1/IO79UDB1
T20	NC
T21	NC
T22	NC

FG484	
Pin Number	**AGL400 Function**
V15	IO85RSB2
V16	GDB2/IO81RSB2
V17	TDI
V18	NC
V19	TDO
V20	GND
V21	NC
V22	NC
W1	NC
W2	NC
W3	NC
W4	GND
W5	IO126RSB2
W6	FF/GEB2/IO133RSB2
W7	IO124RSB2
W8	IO116RSB2
W9	IO113RSB2
W10	IO107RSB2
W11	IO105RSB2
W12	IO102RSB2
W13	IO97RSB2
W14	IO92RSB2
W15	GDC2/IO82RSB2
W16	IO86RSB2
W17	GDA2/IO80RSB2
W18	TMS
W19	GND
W20	NC
W21	NC
W22	NC
Y1	VCCIB3
Y2	NC
Y3	NC
Y4	NC
Y5	GND
Y6	NC

FG484	
Pin Number	**AGL400 Function**
Y7	NC
Y8	VCC
Y9	VCC
Y10	NC
Y11	NC
Y12	NC
Y13	NC
Y14	VCC
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB1

FG484	
Pin Number	**AGL600 Function**
V15	IO96RSB2
V16	GDB2/IO90RSB2
V17	TDI
V18	GNDQ
V19	TDO
V20	GND
V21	NC
V22	NC
W1	NC
W2	IO148PDB3
W3	NC
W4	GND
W5	IO137RSB2
W6	FF/GEB2/IO142RSB2
W7	IO134RSB2
W8	IO125RSB2
W9	IO123RSB2
W10	IO118RSB2
W11	IO115RSB2
W12	IO111RSB2
W13	IO106RSB2
W14	IO102RSB2
W15	GDC2/IO91RSB2
W16	IO93RSB2
W17	GDA2/IO89RSB2
W18	TMS
W19	GND
W20	NC
W21	NC
W22	NC
Y1	VCCIB3
Y2	IO148NDB3
Y3	NC
Y4	NC
Y5	GND
Y6	NC

FG484	
Pin Number	**AGL1000 Function**
C21	NC
C22	VCCIB1
D1	IO219PDB3
D2	IO220NDB3
D3	NC
D4	GND
D5	GAA0/IO00RSB0
D6	GAA1/IO01RSB0
D7	GAB0/IO02RSB0
D8	IO16RSB0
D9	IO22RSB0
D10	IO28RSB0
D11	IO35RSB0
D12	IO45RSB0
D13	IO50RSB0
D14	IO55RSB0
D15	IO61RSB0
D16	GBB1/IO75RSB0
D17	GBA0/IO76RSB0
D18	GBA1/IO77RSB0
D19	GND
D20	NC
D21	NC
D22	NC
E1	IO219NDB3
E2	NC
E3	GND
E4	GAB2/IO224PDB3
E5	GAA2/IO225PDB3
E6	GNDQ
E7	GAB1/IO03RSB0
E8	IO17RSB0
E9	IO21RSB0
E10	IO27RSB0
E11	IO34RSB0
E12	IO44RSB0